

INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE

Features

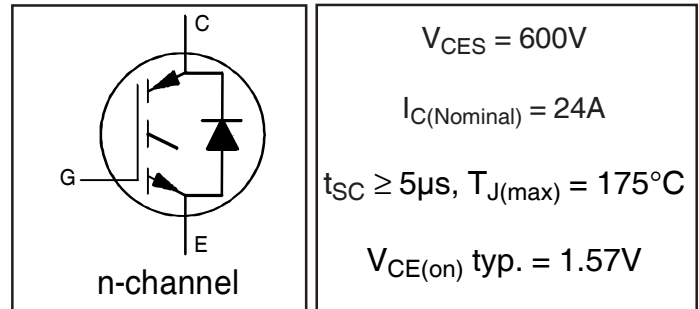
- Low $V_{CE(on)}$ Trench IGBT Technology
- Low Switching Losses
- 5 μ s SCSOA
- Square RBSOA
- 100% of The Parts Tested for I_{LM} ①
- Positive $V_{CE(on)}$ Temperature Coefficient.
- Ultra Fast Soft Recovery Co-pak Diode
- Lead-Free, RoHS Compliant
- Automotive Qualified *

Benefits

- High Efficiency in a Wide Range of Applications
- Suitable for a Wide Range of Switching Frequencies due to Low $V_{CE(ON)}$ and Low Switching Losses
- Rugged Transient Performance for Increased Reliability
- Excellent Current Sharing in Parallel Operation
- Low EMI

Applications

- Air Conditioning Compressor
- EV Inverter
- Battery charger
- DC-DC converter

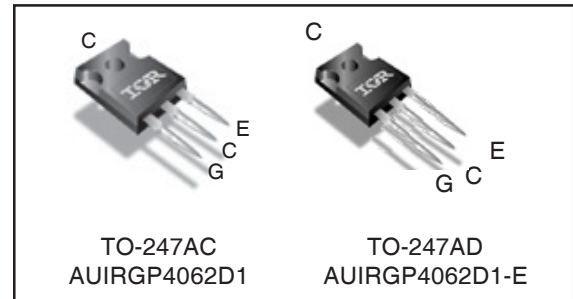


$$V_{CES} = 600V$$

$$I_{C(Nominal)} = 24A$$

$$t_{SC} \geq 5\mu s, T_{J(max)} = 175^{\circ}C$$

$$V_{CE(on)} \text{ typ.} = 1.57V$$



G	C	E
Gate	Collector	Emitter

Ordering Information

Base part number	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRGP4062D1	TO-247AC	Tube	25	AUIRGP4062D1
AUIRGP4062D1-E	TO-247AD	Tube	25	AUIRGP4062D1-E

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^{\circ}C$	Continuous Collector Current	55	A
$I_C @ T_C = 100^{\circ}C$	Continuous Collector Current	36	
$I_{NOMINAL}$	Nominal Current	24	
I_{CM}	Pulse Collector Current, $V_{GE} = 15V$	72	
I_{LM}	Clamped Inductive Load Current, $V_{GE} = 20V$ ①	96	
$I_F @ T_C = 25^{\circ}C$	Diode Continuous Forward Current	55	
$I_F @ T_C = 100^{\circ}C$	Diode Continuous Forward Current	36	V
I_{FM}	Diode Maximum Forward Current ②	96	
V_{GE}	Continuous Gate-to-Emitter Voltage	± 20	V
	Transient Gate-to-Emitter Voltage	± 30	
$P_D @ T_C = 25^{\circ}C$	Maximum Power Dissipation	217	W
$P_D @ T_C = 100^{\circ}C$	Maximum Power Dissipation	109	
T_J	Operating Junction and	-55 to +175	$^{\circ}C$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec. (1.6mm from case)	300	
	Mounting Torque, 6-32 or M3 Screw	10 lbf·in (1.1N·m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance Junction-to-Case (IGBT) ③	---	---	0.69	$^{\circ}C/W$
$R_{\theta JC}$ (Diode)	Thermal Resistance Junction-to-Case (Diode) ③	---	---	1.2	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink (flat, greased surface)	---	0.24	---	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	---	40	---	

*Qualification standards can be found at <http://www.irf.com/>

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 100\mu A$ ④
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.3	—	V/ $^\circ\text{C}$	$V_{GE} = 0V, I_C = 10mA$ (25 $^\circ\text{C}$ -175 $^\circ\text{C}$)
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	1.57	1.77	V	$I_C = 24A, V_{GE} = 15V, T_J = 25^\circ\text{C}$
		—	1.87	—		$I_C = 24A, V_{GE} = 15V, T_J = 150^\circ\text{C}$
		—	1.94	—		$I_C = 24A, V_{GE} = 15V, T_J = 175^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	4.0	—	6.5	V	$V_{CE} = V_{GE}, I_C = 700\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Threshold Voltage temp. coefficient	—	-17	—	mV/ $^\circ\text{C}$	$V_{CE} = V_{GE}, I_C = 1.0mA$ (25 $^\circ\text{C}$ - 175 $^\circ\text{C}$)
g_{fe}	Forward Transconductance	—	12	—	S	$V_{CE} = 50V, I_C = 24A, PW = 20\mu s$
I_{CES}	Collector-to-Emitter Leakage Current	—	1.0	25	μA	$V_{GE} = 0V, V_{CE} = 600V$
		—	3.5	—	mA	$V_{GE} = 0V, V_{CE} = 600V, T_J = 175^\circ\text{C}$
V_{FM}	Diode Forward Voltage Drop	—	1.57	—	V	$I_F = 24A$
		—	1.40	—		$I_F = 19A$
		—	1.47	—		$I_F = 24A, T_J = 175^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	51	77	nC	$I_C = 24A$
Q_{ge}	Gate-to-Emitter Charge (turn-on)	—	14	21		$V_{GE} = 15V$
Q_{gc}	Gate-to-Collector Charge (turn-on)	—	21	32		$V_{CC} = 400V$
E_{on}	Turn-On Switching Loss	—	532	754	μJ	$I_C = 24A, V_{CC} = 400V, V_{GE} = 15V$
E_{off}	Turn-Off Switching Loss	—	311	526		$R_G = 10\Omega, L = 210\mu H, T_J = 25^\circ\text{C}$
E_{total}	Total Switching Loss	—	843	1280		Energy losses include tail & diode reverse recovery
$t_{d(on)}$	Turn-On delay time	—	19	36	ns	$I_C = 24A, V_{CC} = 400V, V_{GE} = 15V$
t_r	Rise time	—	24	41		$R_G = 10\Omega, L = 210\mu H, T_J = 25^\circ\text{C}$
$t_{d(off)}$	Turn-Off delay time	—	90	109		
t_f	Fall time	—	23	40		
E_{on}	Turn-On Switching Loss	—	726	—	μJ	$I_C = 24A, V_{CC} = 400V, V_{GE} = 15V$
E_{off}	Turn-Off Switching Loss	—	549	—		$R_G = 10\Omega, L = 210\mu H, T_J = 175^\circ\text{C}$ ④
E_{total}	Total Switching Loss	—	1275	—		Energy losses include tail & diode reverse recovery
$t_{d(on)}$	Turn-On delay time	—	12	—	ns	$I_C = 24A, V_{CC} = 400V, V_{GE} = 15V$
t_r	Rise time	—	23	—		$R_G = 10\Omega, L = 200\mu H, L_S = 150nH$
$t_{d(off)}$	Turn-Off delay time	—	92	—		$T_J = 175^\circ\text{C}$
t_f	Fall time	—	84	—		
C_{ies}	Input Capacitance	—	1487	—	pF	$V_{GE} = 0V$
C_{oes}	Output Capacitance	—	118	—		$V_{CC} = 30V$
C_{res}	Reverse Transfer Capacitance	—	44	—		$f = 1.0MHz$
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				$T_J = 175^\circ\text{C}, I_C = 96A$ $V_{CC} = 480V, V_p \leq 600V$ $R_G = 10\Omega, V_{GE} = +20V$ to 0V
SCSOA	Short Circuit Safe Operating Area	5	—	—	μs	$V_{CC} = 400V, V_p \leq 600V$ $R_G = 10\Omega, V_{GE} = +15V$ to 0V
E_{rec}	Reverse Recovery Energy of the Diode	—	773	—	μJ	$T_J = 175^\circ\text{C}$
t_{rr}	Diode Reverse Recovery Time	—	102	—	ns	$V_{CC} = 400V, I_F = 24A$
I_{rr}	Peak Reverse Recovery Current	—	32	—	A	$V_{GE} = 15V, R_G = 10\Omega, L = 210\mu H$

Notes:

- ① $V_{CC} = 80\% (V_{CES}), V_{GE} = 20V, L = 210\mu H, R_G = 50\Omega$.
- ② Pulse width limited by max. junction temperature.
- ③ R_θ is measured at T_J of approximately 90 $^\circ\text{C}$.
- ④ Maximum limits are based on statistical sample size characterization.

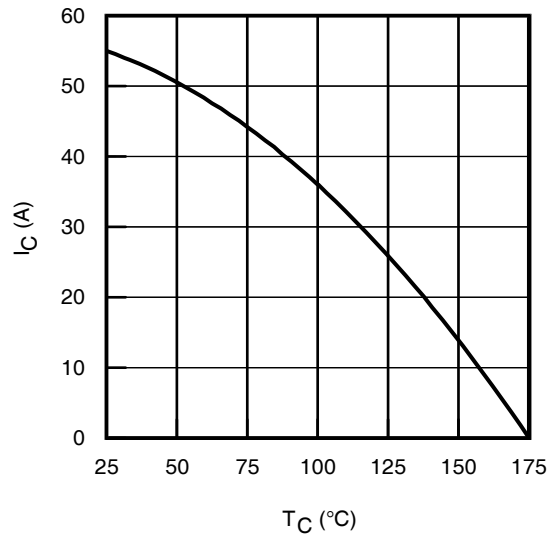


Fig. 1 - Maximum DC Collector Current vs. Case Temperature

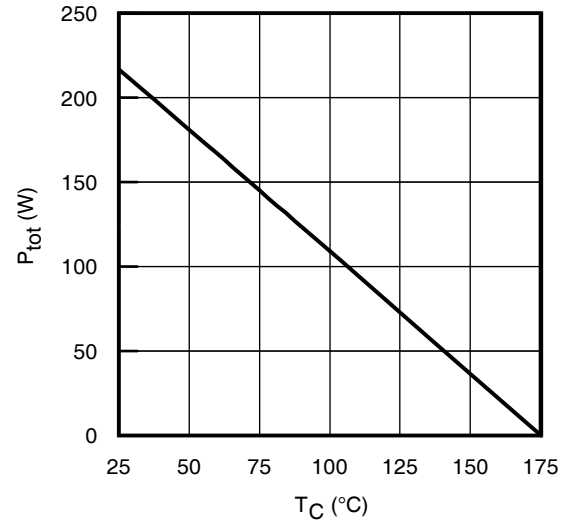


Fig. 2 - Power Dissipation vs. Case Temperature

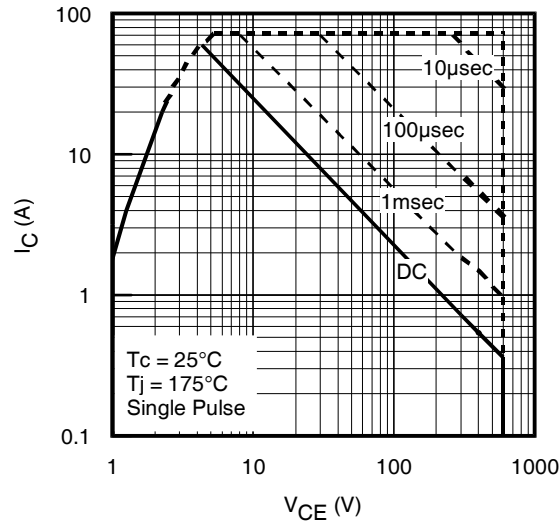


Fig. 3 - Forward SOA
 $T_C = 25^\circ\text{C}$, $T_J \leq 175^\circ\text{C}$; $V_{GE} = 15\text{V}$

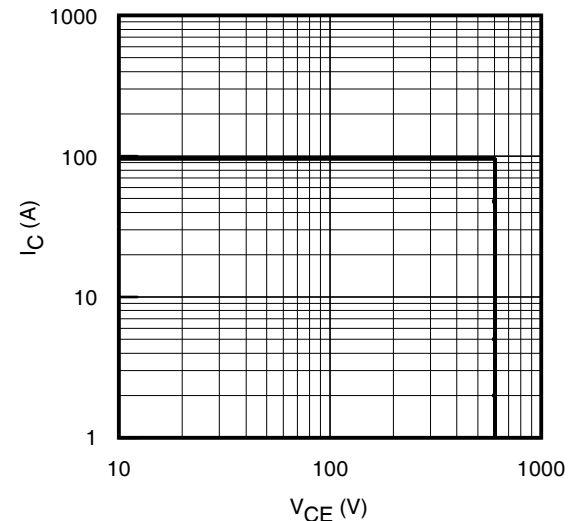


Fig. 4 - Reverse Bias SOA
 $T_J = 175^\circ\text{C}$; $V_{GE} = 20\text{V}$

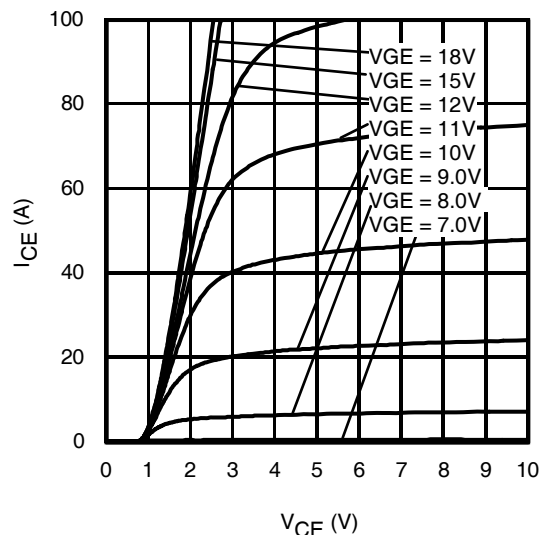


Fig. 5 - Typ. IGBT Output Characteristics
 $T_J = -40^\circ\text{C}$; $t_p = 20\mu\text{s}$

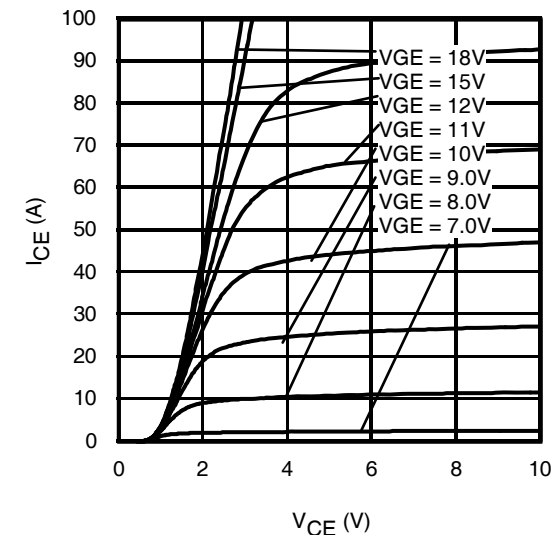


Fig. 6 - Typ. IGBT Output Characteristics
 $T_J = 25^\circ\text{C}$; $t_p = 20\mu\text{s}$

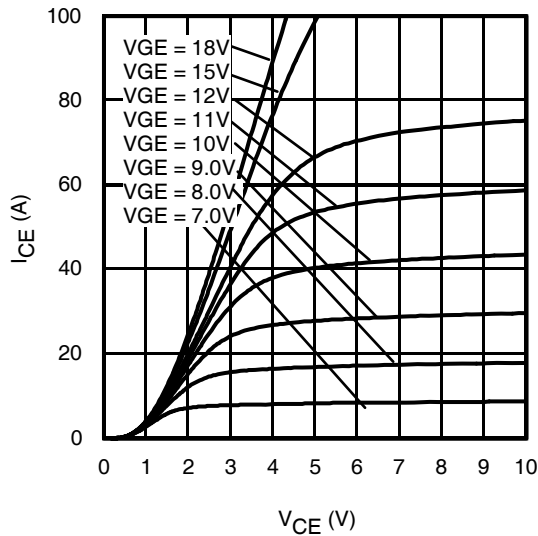


Fig. 7 - Typ. IGBT Output Characteristics
 $T_J = 175^\circ\text{C}$; $t_p = 20\mu\text{s}$

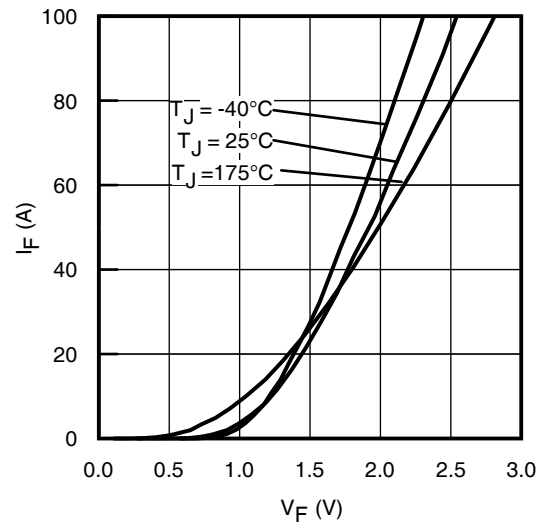


Fig. 8 - Typ. Diode Forward Characteristics
 $t_p = 20\mu\text{s}$

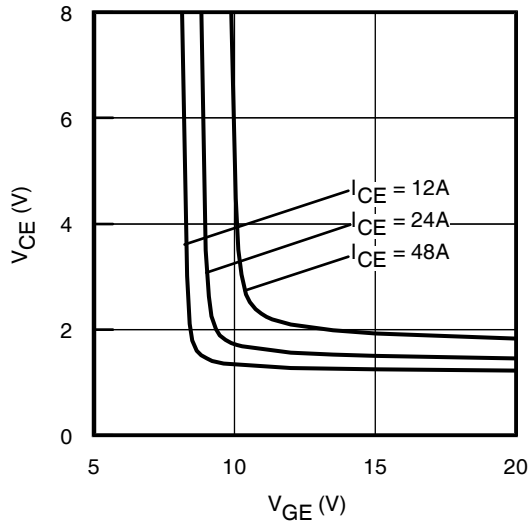


Fig. 9 - Typical V_{CE} vs. V_{GE}
 $T_J = -40^\circ\text{C}$

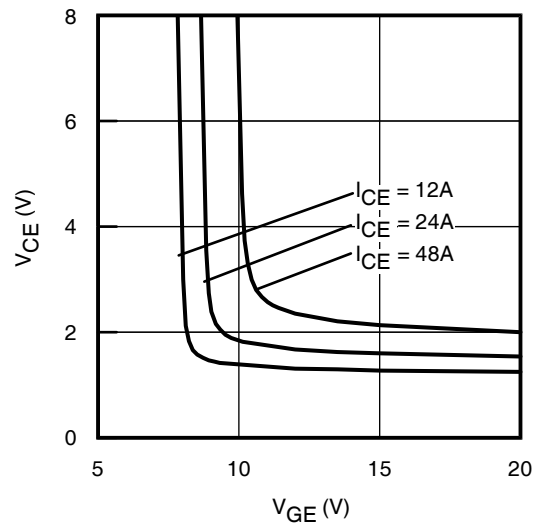


Fig. 10 - Typical V_{CE} vs. V_{GE}
 $T_J = 25^\circ\text{C}$

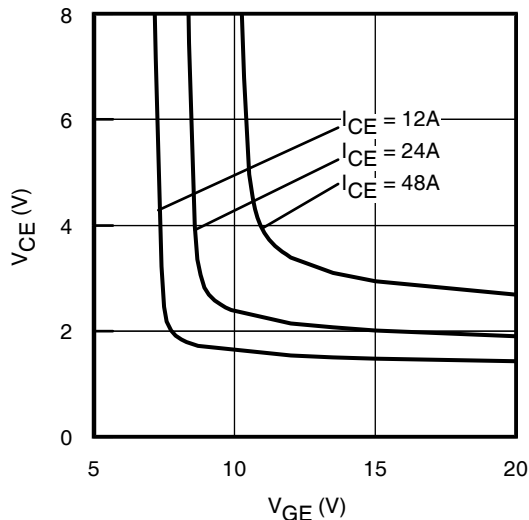


Fig. 11 - Typical V_{CE} vs. V_{GE}
 $T_J = 175^\circ\text{C}$

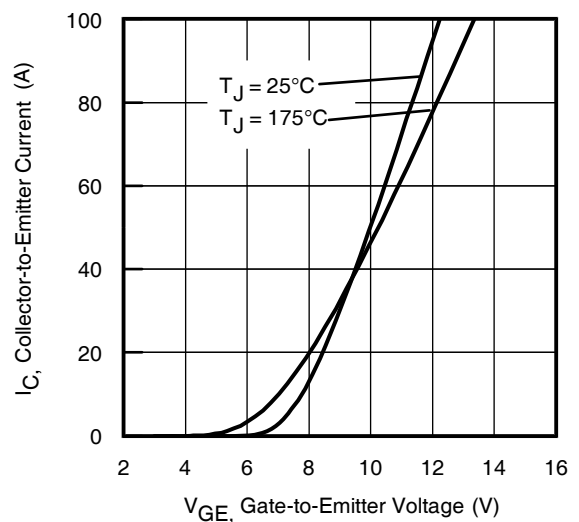
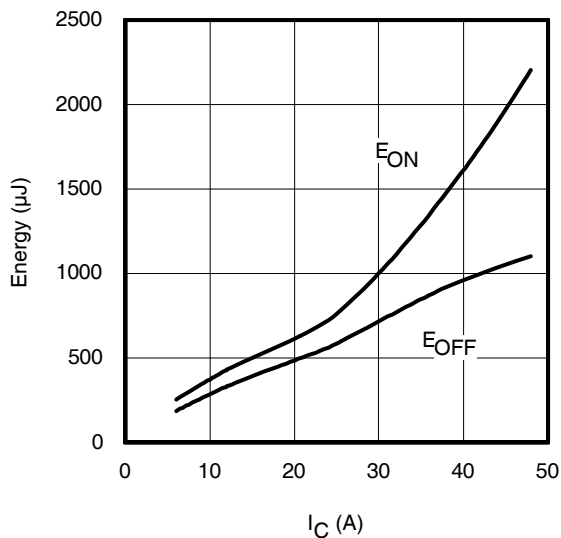
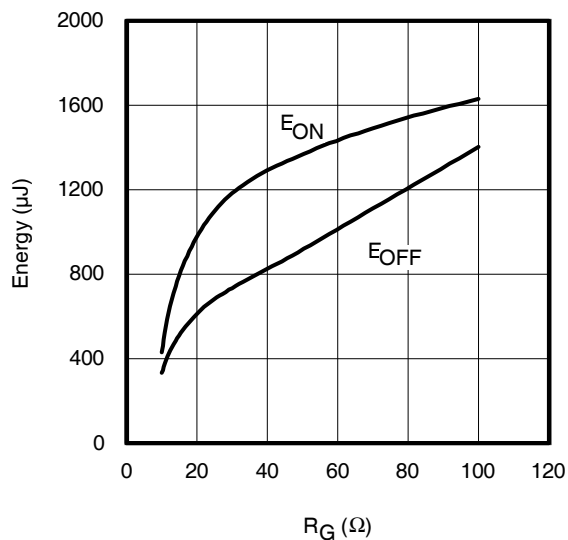
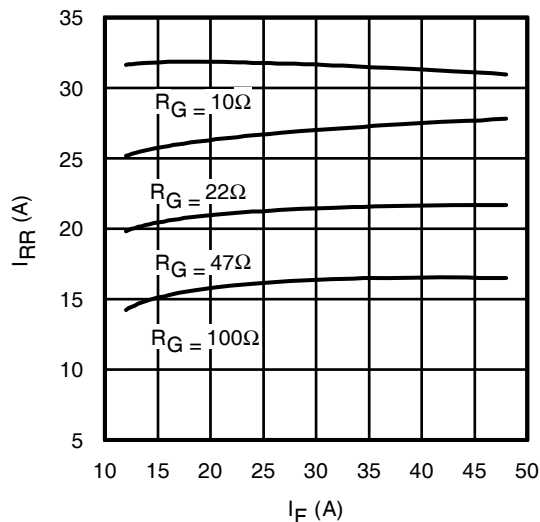
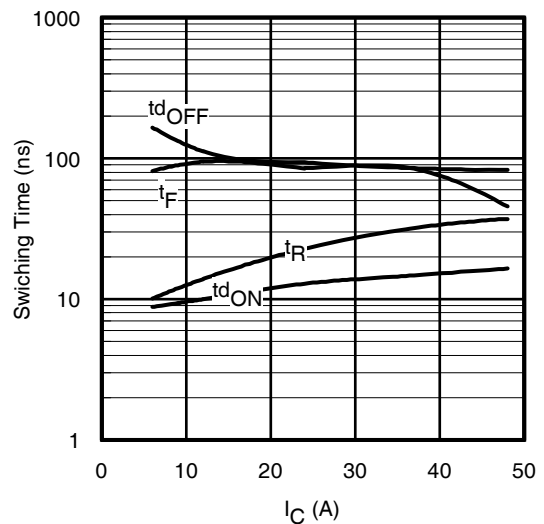
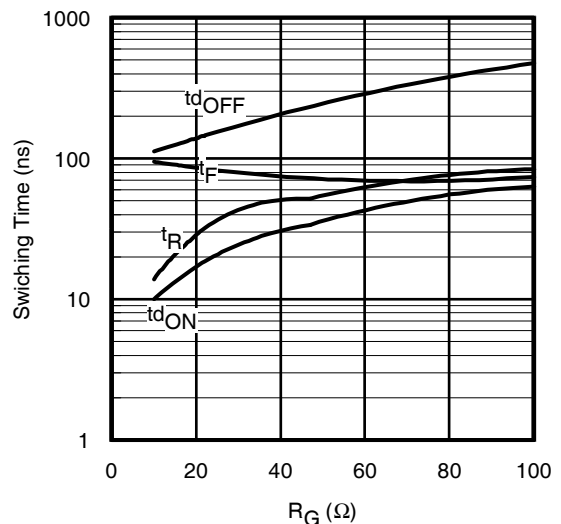
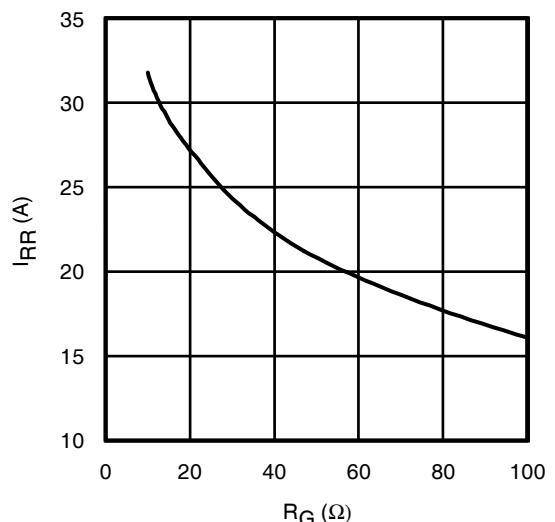


Fig. 12 - Typ. Transfer Characteristics
 $V_{CE} = 50\text{V}$; $t_p = 20\mu\text{s}$


Fig. 13 - Typ. Energy Loss vs. I_C
 $T_J = 175^\circ\text{C}; L = 210\mu\text{H}; V_{CE} = 400\text{V}; R_G = 10\Omega; V_{GE} = 15\text{V}$

Fig. 15 - Typ. Energy Loss vs. R_G
 $T_J = 175^\circ\text{C}; L = 210\mu\text{H}; V_{CE} = 400\text{V}; I_{CE} = 24\text{A}; V_{GE} = 15\text{V}$

Fig. 17 - Typ. Diode I_{RR} vs. I_F
 $T_J = 175^\circ\text{C}$

Fig. 14 - Typ. Switching Time vs. I_C
 $T_J = 175^\circ\text{C}; L = 210\mu\text{H}; V_{CE} = 400\text{V}; R_G = 10\Omega; V_{GE} = 15\text{V}$

Fig. 16 - Typ. Switching Time vs. R_G
 $T_J = 175^\circ\text{C}; L = 210\mu\text{H}; V_{CE} = 400\text{V}; I_{CE} = 24\text{A}; V_{GE} = 15\text{V}$

Fig. 18 - Typ. Diode I_{RR} vs. R_G
 $T_J = 175^\circ\text{C}$

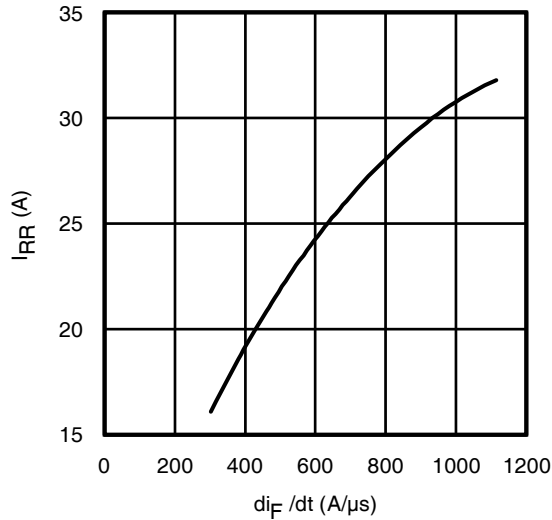


Fig. 19 - Typ. Diode I_{RR} vs. di_F/dt
 $V_{CC} = 400V$; $V_{GE} = 15V$; $I_F = 24A$; $T_J = 175^\circ C$

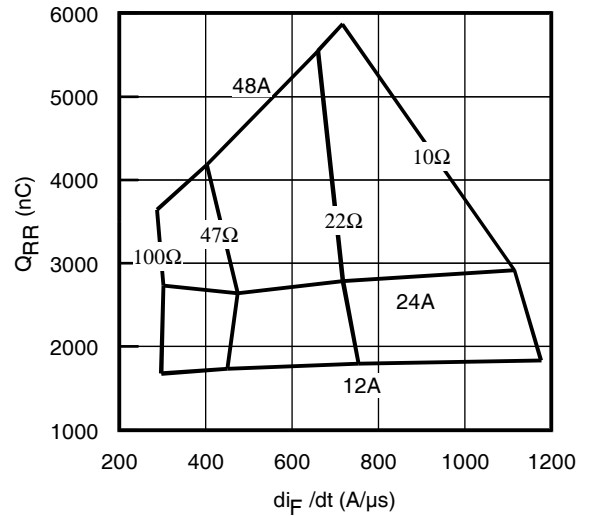


Fig. 20 - Typ. Diode Q_{RR} vs. di_F/dt
 $V_{CC} = 400V$; $V_{GE} = 15V$; $T_J = 175^\circ C$

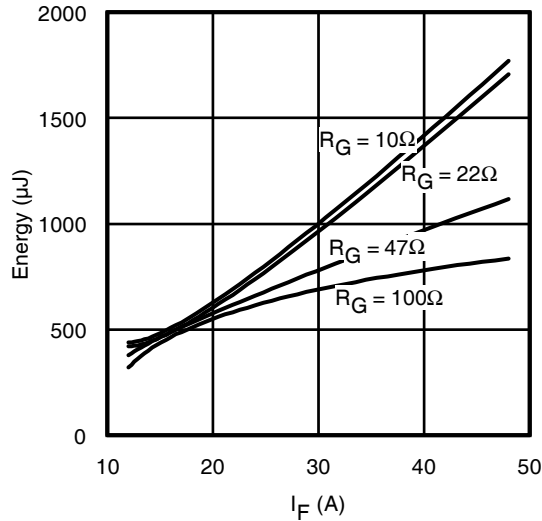


Fig. 21 - Typ. Diode E_{RR} vs. I_F
 $T_J = 175^\circ C$

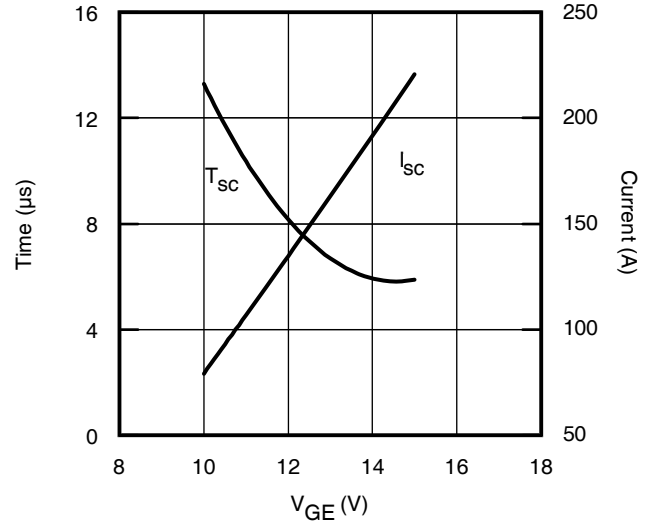


Fig. 22 - V_{GE} vs. Short Circuit Time
 $V_{CC} = 400V$; $T_C = 25^\circ C$

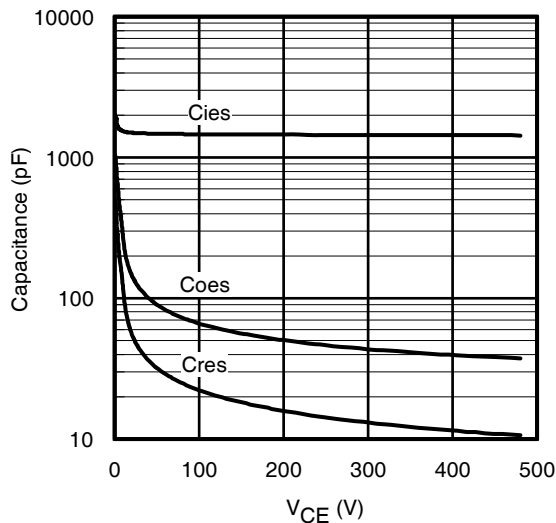


Fig. 23 - Typ. Capacitance vs. V_{CE}
 $V_{GE} = 0V$; $f = 1MHz$

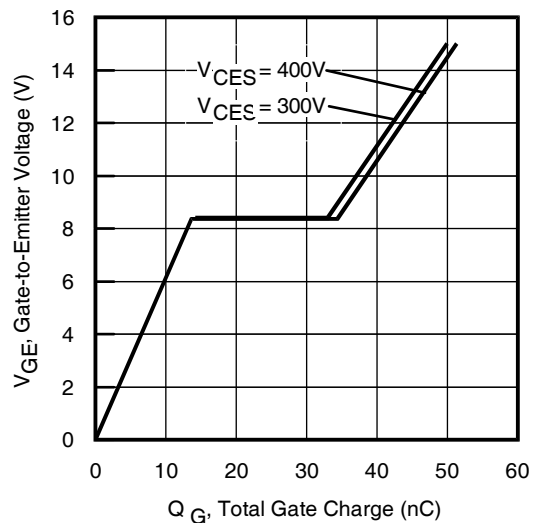


Fig. 24 - Typical Gate Charge vs. V_{GE}
 $I_{CE} = 24A$; $L = 585\mu H$

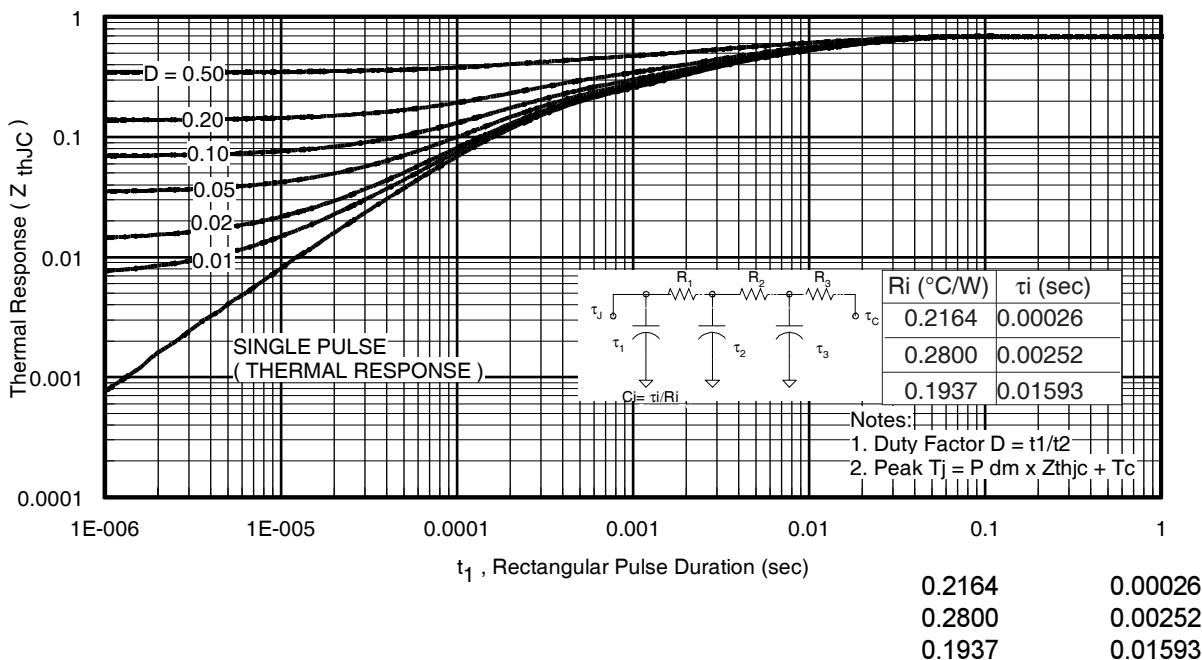


Fig 25. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

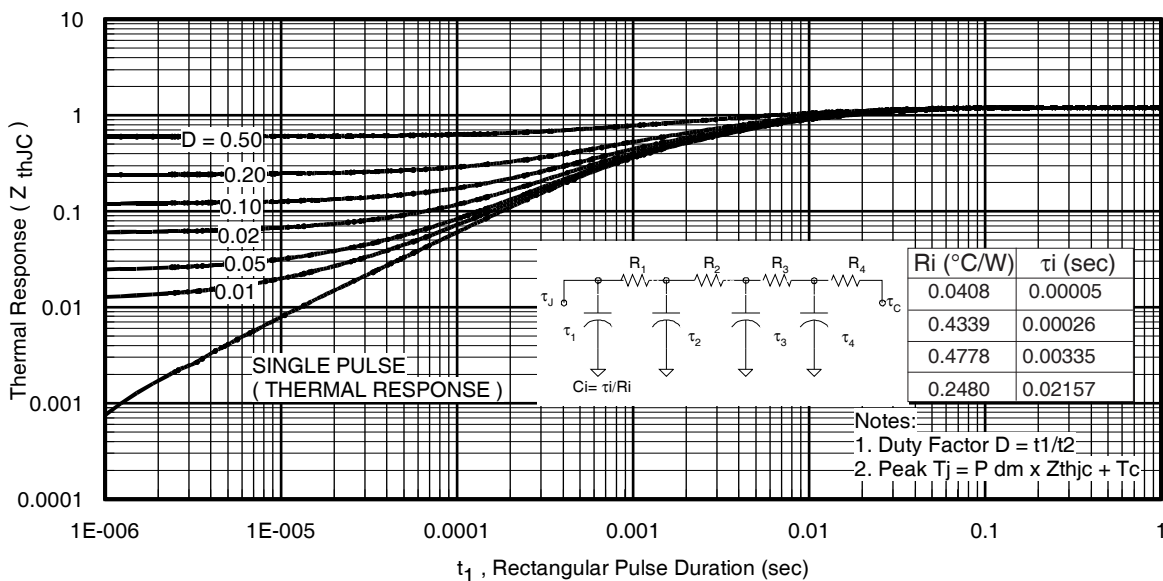
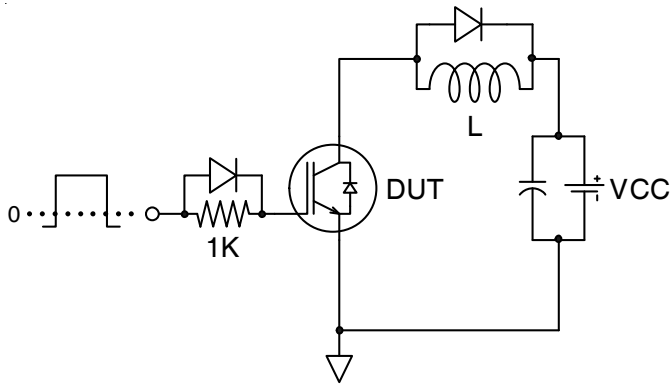
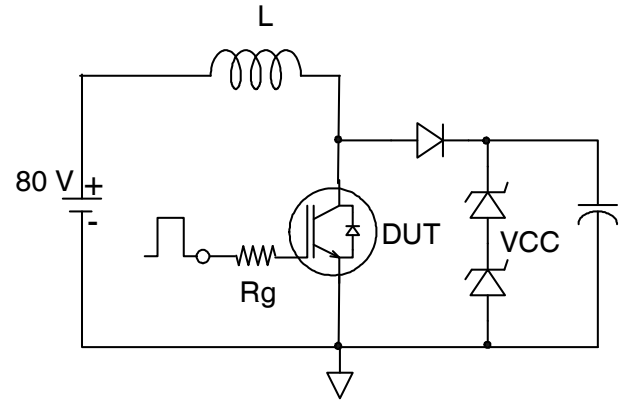
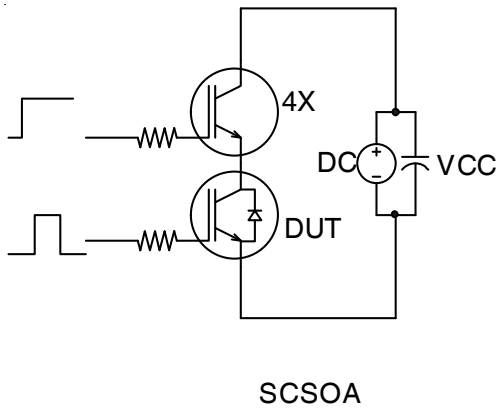
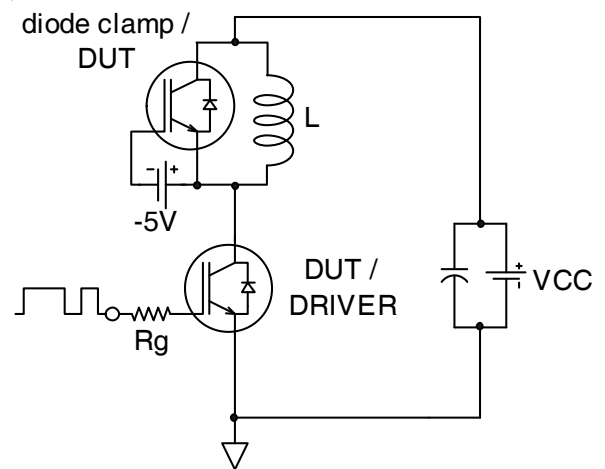
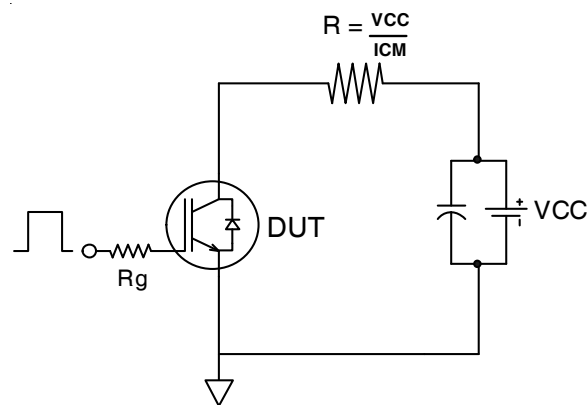


Fig. 26. Maximum Transient Thermal Impedance, Junction-to-Case (DIODE)


Fig.C.T.1 - Gate Charge Circuit (turn-off)

Fig.C.T.2 - RBSOA Circuit

Fig.C.T.3 - S.C. SOA Circuit

Fig.C.T.4 - Switching Loss Circuit

Fig.C.T.5 - Resistive Load Circuit

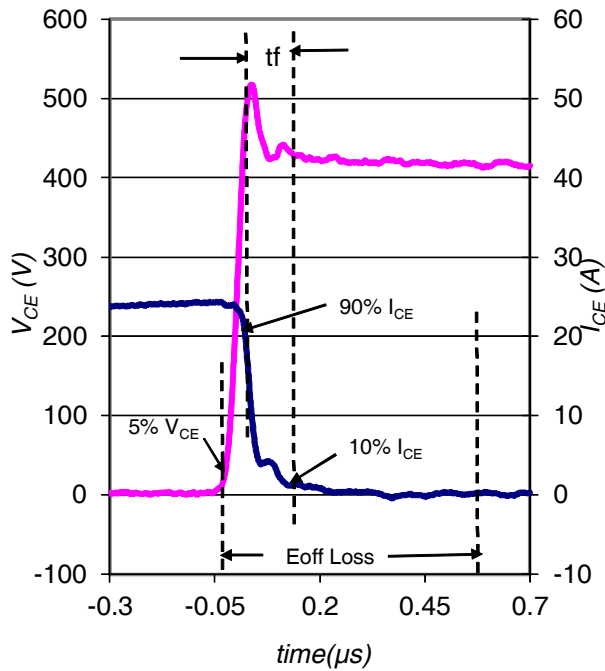


Fig. WF1 - Typ. Turn-off Loss Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

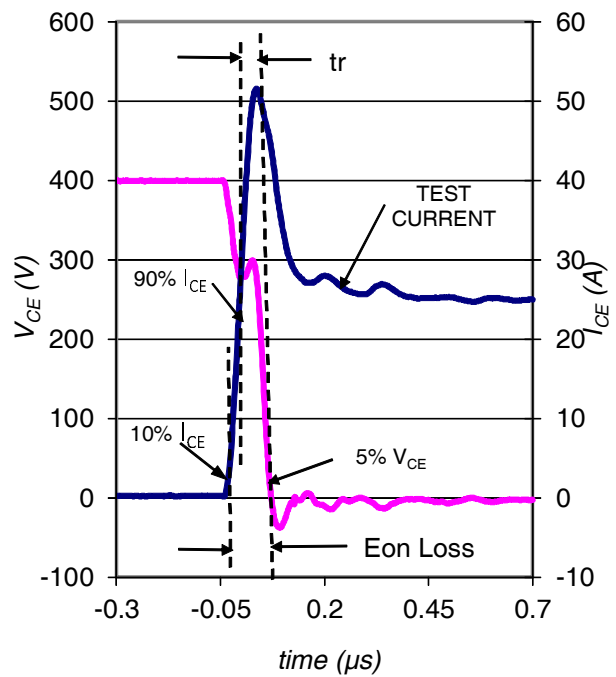


Fig. WF2 - Typ. Turn-on Loss Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

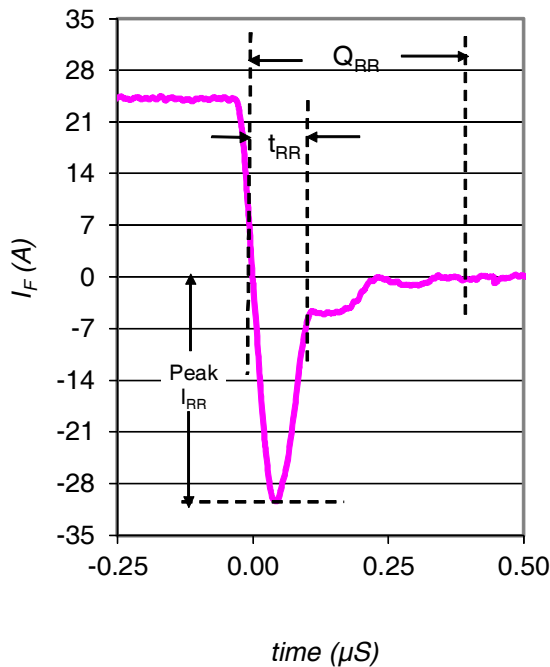


Fig. WF3 - Typ. Diode Recovery Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

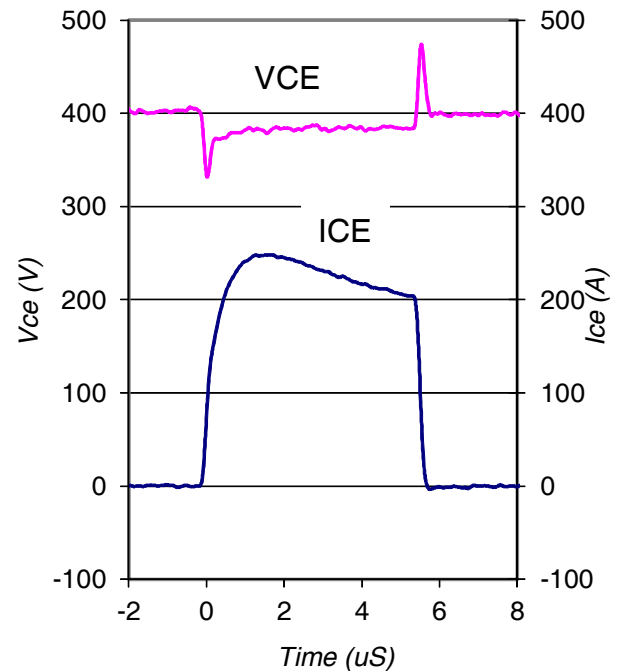
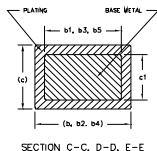


Fig. WF4 - Typ. S.C. Waveform
@ $T_J = 25^\circ\text{C}$ using Fig. CT.3

Dimensions are shown in millimeters (inches)



1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES.
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. ØP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AC.

SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	4
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	5
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	
D1	.515	—	13.08	—	4
D2	.020	.053	0.51	1.35	
D3	1.122	1.161	28.50	29.50	
E	.602	.625	15.29	15.87	
E1	.530	—	13.46	—	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
ek	.010		0.25		
L	.559	.634	14.20	16.10	
L1	.146	.169	3.71	4.29	
pP	.140	.144	3.56	3.66	
eP1	—	.291	—	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

AUIRG4PH50S
AUIRGP4066D1/E
AUIRGP4063D/E
AUIRGP50B60PD1/E
AUIRGP35B60PD/E
AUIRGP4062D1/E
AUIRGP65A20D0
AUIRGP65G20D0
AUIRGP/F66524D0
AUIRGP/F76524D0
AUIRGP/F66548D0
AUIRGP/F76548D0

1.- GATE	1.- ANODE/OPEN
2.- COLLECTOR	2.- CATHODE
3.- EMITTER	3.- ANODE
4.- COLLECTOR	

a) ADDED D3 FOR SPECIAL REQUIREMENT

NOTES, ASSEMBLY:

- WIRE BOND METHOD: ULTRA-SONIC WEDGE BONDING.
- MARKING SPECIFICATION: 23-0014
- EMITTER BOND PAD SIZE: APPROX. .0953 X .108
- CATE BOND PAD SIZE: .0198 X .0219
- ANODE BONDABLE AREA: .0056 X .0056
- WAFER ORIENTATION: DATE (GATE PAD LOCATION IS OPPOSITE OF WAFER FLAT)
- DIE COAT PROCESS ONLY ON DIODE

ITEM	REFERENCE NUMBER	DESCRIPTION	QTY
10	43-9849	DIE COAT (DIODE ONLY)	A ₁
9	43-9807	MOLD COMPOUND (WGD5F-35A)	A ₁
8	44-0071	PBF SOLDER DIP	A ₁
7	44-0199-05	ANODE, BOND MRE, Au / 4/9% Ni DOPED_15_mils	A ₁
6	44-0199-05	EMITTER, BOND MRE, Au / 4/9% Ni DOPED_15_mils	A ₁
5	44-0199-01	GATE, BOND MRE, Au / 4/9% Ni DOPED_5_mils	A ₁
4	67231FAU (01-5697)	GATE 1.0MM ONLY (DI 355-154 X .85 X .002, 80% Au, 20% Ni)	A ₁
3	44-1087	WAFER SIZE 1.0MM, 625 (DI 355-154 X .85, 80% Au, 20% Ni)	A ₁
2	44-7686	SOLDER, DIE ATTACH (2-ALLOY)	A ₁
1	44-0023	LEADFRAME, TO-247 (280 X .457)	A ₁

AURGP4062D1, TO-247 ASSY, IR/EX

1. Dose = 25 units/dose

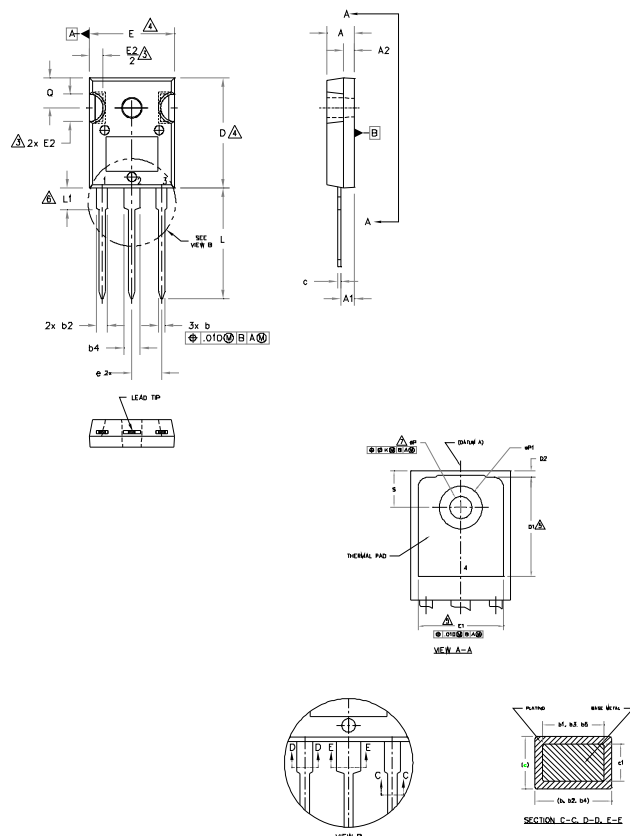
10	43-9887	DE COAT (DGE ONLY)	A/A	
9	43-9809	MOLD COMPOUND (WGF5F-35A)	A/A	
8	44-0071	PBF SOLDER DP	A/A	
7	44-0199-05	ANODE, BOND WIRE, A1/4% Ni DOPED 15_mils	2	
6	44-0199-05	EMITTER, BOND WIRE, A1/4% Ni DOPED 15_mils	2	
5	44-0199-01	GATE, BOND WIRE, A1/4% Ni DOPED 5_mils	1	
4	87231A-01 (-S089)	Q1: 4.00E-22 52 62 52 52 15.5 1.5 0.2 0.08 0.01 0.4 120mV/10mV	1	
3	43-1067	SHIELDING CAP 1 30000V 0.01 50% 30% 10% 100mV/10mV	1	
2	43-7698	SOLDER, DE ATTACH (-ALLOY)	1	
1	44-0223	LEADFRAME, TO-247 (280 X 457)	1	
ITEM	REFERENCE	NUMBER	D E S C R I P T I O N	QTY
AURPG406201, TO-247 ASSEMB, IRMXE				

ALL DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS]

May 02, 2013

TO-247AD Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES.
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127)
PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. ØP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE
DIAMETER OF .154 INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AD.

SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.190	.203	4.83	5.13	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	
D1	.515	—	13.08	—	4
D2	.020	.053	0.51	1.35	
E	.602	.625	15.29	15.87	4
E1	.530	—	13.46	—	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
Øk	.010		0.25		
L	.780	.827	19.57	21.00	
L1	.146	.169	3.71	4.29	
L2	.140	.144	3.56	3.66	
ØP1	—	.291	—	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

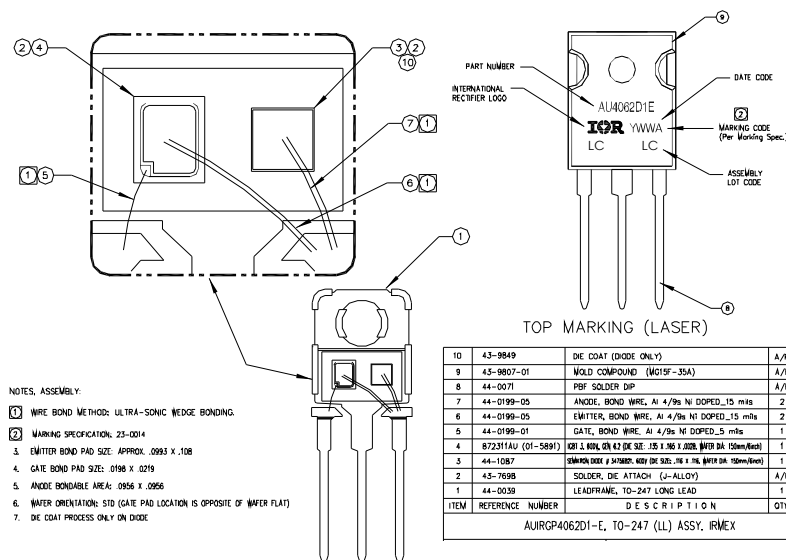
IGBTs, CoPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

DIODES

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

TO-247AD Part Marking Information



NOTES ASSEMBLY:

1. WIRE BOND METHOD: ULTRA-SONIC WEDGE BONDING.
2. MARKING SPECIFICATION: 23-0014
3. EMITTER BOND PAD SIZE: APPROX. .093 X .108
4. GATE BOND PAD SIZE: .0198 X .0219
5. ANODE BONDABLE AREA: .0956 X .0956
6. WAFER ORIENTATION: STD (GATE PAD LOCATION IS OPPOSITE OF WAFER FLAT)
7. THE COAT PROCESS ONLY ON DIODE

NOTES. PACKAGING

1. TUBE - 25 UNITS/TUBE

ALL DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS]

TOP MARKING (LASER)

10	43-9849	DIE COAT (DIODE ONLY)	A/
9	45-9807-01	MOLD COMPOUND (W01F-JSA)	A/
8	44-0071	PBF SOLDER PIND	A/
7	44-0199-05	ANODE, BOND WIRE, A1 4/96 NI DOPED, .15_mils	B/
6	44-0199-05	EMITTER, BOND WIRE, A1 4/96 Ni DOPED, .15_mils	B/
5	44-0199-01	GATE, BOND WIRE, A1 4/96 Ni DOPED, .5_mils	B/
4	87231A1A (Q1-5898)	Q1 RING, ON DIE SET SEE .155 1.363 .0028, (SEE DRAWN) (SEE FILE)	C/
3	44-087	SOLDER BRIDGE TO SUBSTRATE, (SEE SUB), (SEE DRAWN) (SEE FILE)	C/
2	45-7698	CONDUCTIVE PASTE, (SEE Q1-5898)	A/
1	44-0039	LEADFRAME, TO-DAY LONG LEAD	A/
ITEM	REFERENCE NUMBER	DESCRIPTION	QTY

AUIRGP4062D1-E, TO-247 (LL) ASSY. IRME

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Qualification Information[†]

Qualification Level		Automotive (per AEC-Q101) ^{††}	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		3L-TO-247AC	N/A
		3L-TO-247AD	
ESD	Machine Model	Class M4 (+/- 700V) (per AEC-Q101-002)	
	Human Body Model	Class H1C (+/- 2000V) (per AEC-Q101-001)	
	Charged Device Model	Class C5(+/- 2000V) (per AEC-Q101-005)	
RoHS Compliant		Yes	

[†] Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/>

^{††} Highest passing voltage.

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For technical support, please contact IR’s Technical Assistance Center

<http://www.irf.com/technical-info/>

WORLD HEADQUARTERS:

101 N. Sepulveda Blvd., El Segundo, California 90245

Tel: (310) 252-7105